

TITLE:
RESISTIVE RANDOM ACCESS MEMORY AND METHOD OF MANUFACTURING
THE SAME

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ABSTRACT

A resistive random access memory includes a first electrode, a second electrode, a dielectric layer, a protection layer, and at least one switching layer. The dielectric layer is formed on the first electrode. The dielectric layer has an opening exposing a portion of
10 the first electrode. The protection layer is disposed on sidewalls of the opening. The switching layer is disposed on the exposed portion of the first electrode and exposes a portion of sidewalls of the protection layer. The second electrode is at least one conductive layer and is disposed on the switching layer in the opening.

15 [FIG. 1]